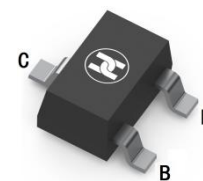
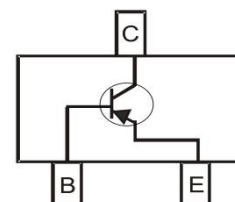


BIPOLAR TRANSISTOR (PNP)
FEATURES

- Complementary to MMST2222A
- Epitaxial planar die construction
- Surface Mount device

MECHANICAL DATA

- Case: SOT-323
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.008 grams (approximate)


SOT-323

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

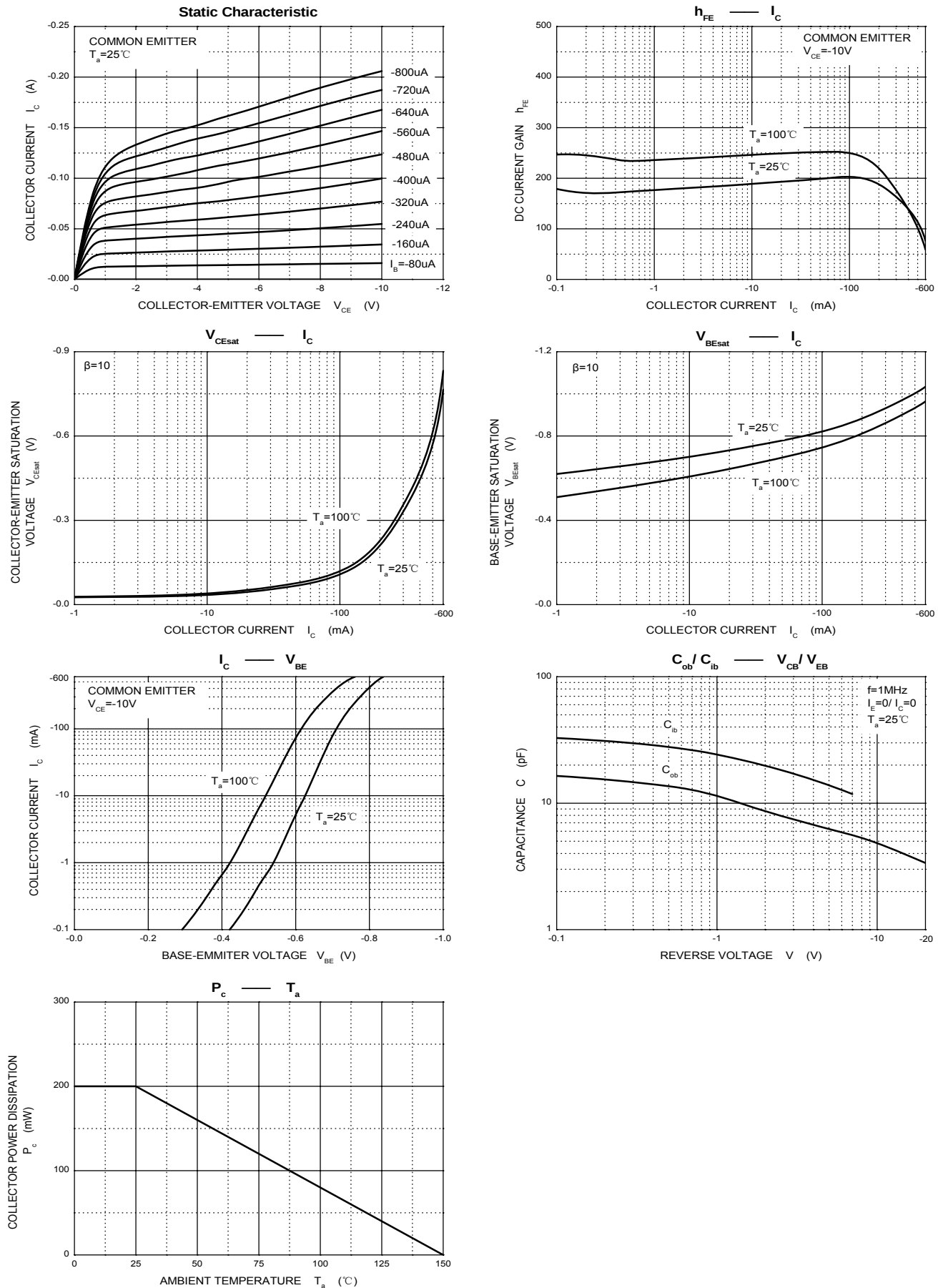
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

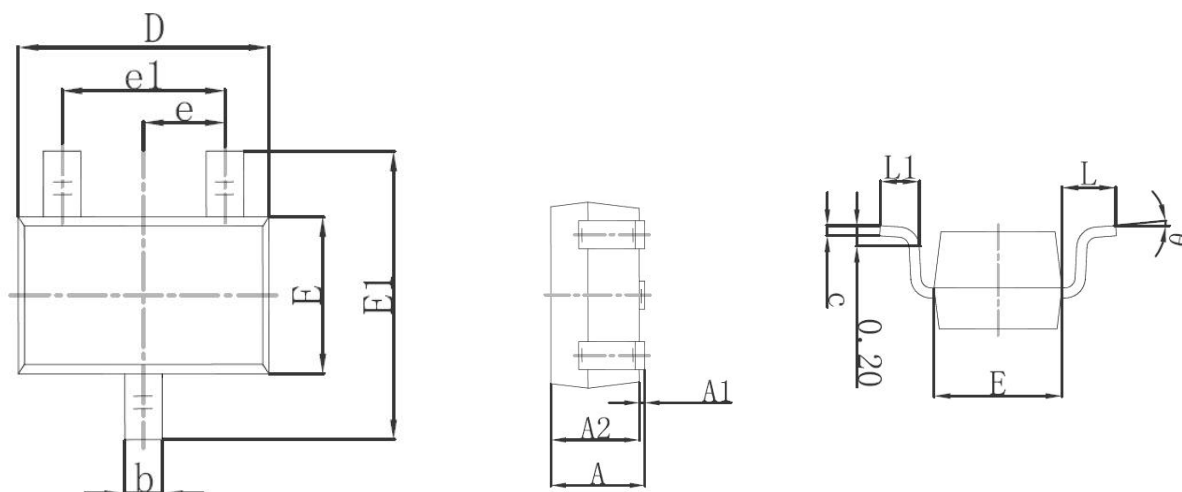
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Collector-base breakdown voltage	V _{(BR)CBO}	-60			V	I _C =-10uA, I _E =0
Collector-emitter breakdown voltage	V _{(BR)CEO}	-60			V	I _C =-10mA, I _B =0
Emitter-base breakdown voltage	V _{(BR)EBO}	-5			V	I _E =-10uA, I _C =0
Collector cut-off current	I _{CBO}			-100	nA	V _{CB} =-50V, I _E =0
Collector cut-off current	I _{CEB}			-100	nA	V _{CB} =-30V, I _B =0
Emitter cut-off current	I _{EBO}			-100	nA	V _{EB} =-3V, I _C =0
DC current gain	h _{FE1}	75				V _{CE} =-10V, I _C =-0.1mA
	h _{FE2}	100				V _{CE} =-10V, I _C =-1mA
	h _{FE3}	100				V _{CE} =-10V, I _C =-10mA
	h _{FE4}	100		300		V _{CE} =-10V, I _C =-150mA
	h _{FE5}	50				V _{CE} =-10V, I _C =-500mA
Collector-emitter saturation voltage	V _{CE(sat)}			-1.6	V	I _C =-500mA, I _B =-50mA
	V _{CE(sat)}			-0.4	V	I _C =-150mA, I _B =-15mA
Base-emitter saturation voltage	V _{BE(sat)}			-2.6	V	I _C =-500mA, I _B =-50mA
	V _{BE(sat)}			-1.3	V	I _C =-150mA, I _B =-15mA
Transition frequency	f _T	200			MHz	V _{CE} =-20V, I _C =-50mA, f=100MHz
Output capacitance	C _{ob}			8	pF	V _{CB} =-10V, I _E =0, f=0.1MHz
Input capacitance	C _{ib}			30	pF	V _{EB} =-2V, I _C =0, f=0.1MHz
Delay time	t _d			10	ns	V _{CC} =-30V, I _C =-150mA,
Rise time	t _r			40	ns	V _{BE(OFF)} =-1.5V, I _{B1} =-15mA
Storage time	t _s			80	ns	V _{CC} =-30V, I _C =-150mA
Fall time	t _f			30	ns	I _{B1} =I _{B2} =-15mA

Marking: K3F

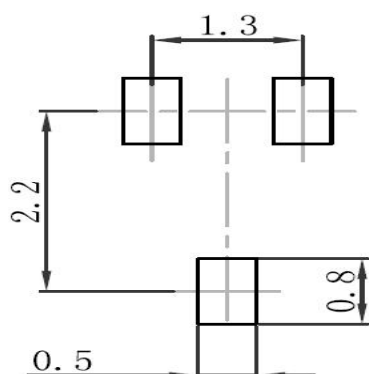
BIPOLAR TRANSISTOR (PNP)

Typical Characteristics

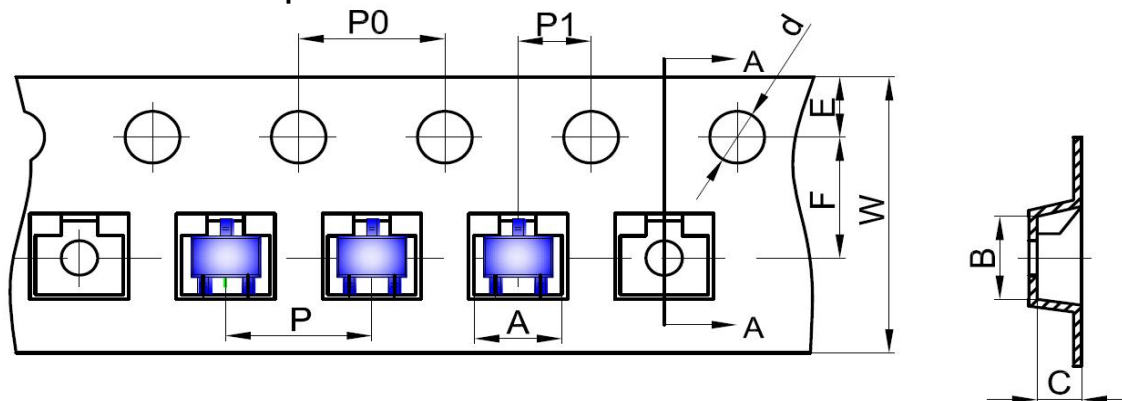


BIPOLAR TRANSISTOR (PNP)
SOT-323 Package Outline Dimensions


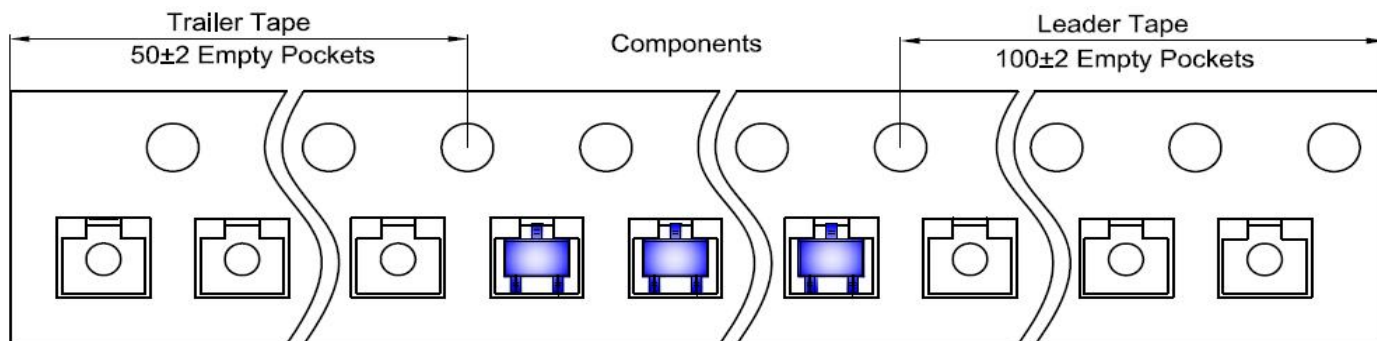
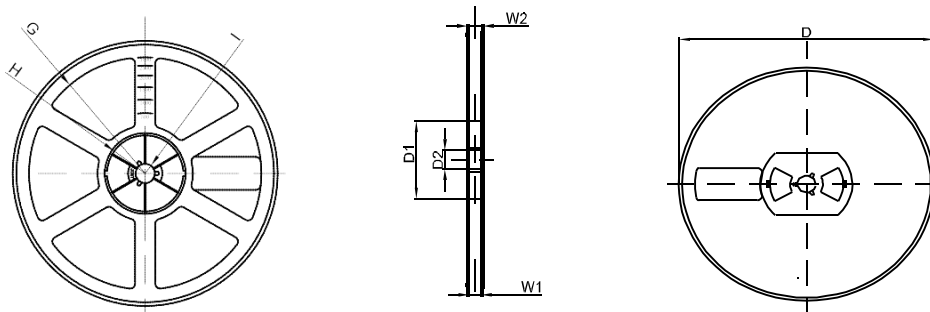
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-323 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

BIPOLAR TRANSISTOR (PNP)
SOT-323 Tape and Reel
SOT-323 Embossed Carrier Tape


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-323	2.25	2.55	1.19	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-323 Tape Leader and Trailer

SOT-323 Reel


DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1